
ERRATA

Simple Scheme for Deriving Atomic Force Constants: Application to SiC. D. H. LEE and J. D. JOANNOPOULOS [Phys. Rev. Lett. 48, 1846 (1982)].

Equation (7) was developed with the assumption that the density of states was zero at the Fermi level and is valid for insulating systems, such as SiC, but not for metallic systems. When contributions from possible variations in the Fermi level are included, we obtain for metallic systems the equation

$$\frac{\partial^2 E_{BS}}{\partial x_\alpha^i \partial x_\beta^j} = -\frac{1}{\pi} \int_{-\infty}^{\epsilon_F^0} d\epsilon \operatorname{Im} \operatorname{Tr} \left[G_B(\epsilon) \frac{\partial^2 H}{\partial x_\alpha^i \partial x_\beta^j} + G_B(\epsilon) \frac{\partial H}{\partial x_\alpha^i} G_B(\epsilon) \frac{\partial H}{\partial x_\beta^j} \right] \\ + \frac{1}{\pi^2} \frac{\operatorname{Im} \operatorname{Tr}[G_B(\epsilon_F^0) \partial H / \partial x_\alpha^i] \operatorname{Im} \operatorname{Tr}[G_B(\epsilon_F^0) \partial H / \partial x_\beta^j]}{D_0(\epsilon_F^0)}.$$

Here ϵ_F^0 is the unperturbed Fermi energy and $D_0(\epsilon_F^0)$ is the unperturbed density of states at the Fermi level.

Test of Time-Reversal Symmetry in the β Decay of ^{19}Ne . A. L. HALLIN, F. P. CALAPRICE, D. W. MACARTHUR, L. E. PIILONEN, M. B. SCHNEIDER, and D. F. SCHREIBER [Phys. Rev. Lett. 52, 337 (1984)].

On p. 337, the value for the asymmetry parameter given in the fifth line of the abstract should be $D = 0.0004 \pm 0.0008$. This is the value which is correctly reported on p. 340.

Schottky Barrier Heights and the Continuum of Gap States. J. TERSOFF [Phys. Rev. Lett. 52, 465 (1984)].

Through an editorial error, the manuscript published was not the final version; among other differences, the final version contained the following discussion of recent experimental results of Tung¹:

Schottky barrier heights are generally rather in-

sensitive to interface orientation and structure. However, for perfectly epitaxial NiSi₂-Si(111) interfaces, Tung¹ has found a remarkable 0.14-eV difference in barrier height between the so-called *A* and *B* interfaces, which differ only by a 180° rotation. The structure is *locally* fcc (diamond) at the *A* interface, but is better described as hexagonal (wurtzite) at the *B* interface. Repeating the calculation above for hexagonal Si (using Joannopoulos and Cohen's² value of 0.85 eV for the band gap, and assuming that the valence-band maximum is the same for both Si structures²), one finds that the valence-conduction crossover energy falls about 0.11 eV lower than in fcc Si. Since the MIGS pinning occurs in this locally hexagonal region, E_F should be pinned roughly that much lower at the *B* interface than at the *A* interface, giving the larger barrier. Thus the model *quantitatively* explains Tung's result.

¹R. T. Tung, Phys. Rev. Lett. 52, 461 (1984). The NiSi₂-Si(111) interface structure is discussed in R. T. Tung, J. M. Gibson, and J. M. Poate, Phys. Rev. Lett. 50, 429 (1983).

²J. D. Joannopoulos and M. L. Cohen, Phys. Rev. B 7, 2644 (1973).

Isotopically Selective Condensation and Infrared-Laser-Assisted Gas-Dynamic Isotope Separation.
J.-M. ZELLWEGER, J.-M. PHILIPPOZ, P. MELINON,
R. MONOT, and H. VAN DEN BERGH [Phys. Rev.
Lett. 52, 522 (1984)].

The two sentences following Eq. (6) should read, "where \bar{X} is the average mole fraction of the desired component, which is ³⁴SF₆ in the experiments described below. Subscript *E* refers to the enriched fraction and *D* to the fraction which is depleted."